

IN THE ABSTRACT OF THE DISCLOSURE:

Please amend the abstract as follows:

ABSTRACT

~~Provided is a~~ The fabrication method of a semiconductor integrated circuit device which comprises forming involves testing using a pushing mechanism that is constructed by forming, over the upper surface of a thin film probe, a reinforcing material having a linear expansion coefficient (thermal expansion coefficient) almost equal to that of a wafer to be tested; forming a groove in the reinforcing material above a contact terminal; placing an elastomer in the groove so that a predetermined amount exceeds projects out of the groove; and disposing a pusher and another elastomer to sandwich the pusher between the elastomers. The present invention makes With the use of such a probe, it is possible to improve the throughput of wafer-level electrical testing of a semiconductor integrated circuit.